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(54) Title: METHOD FOR FORMING THREE-DIMENSIONAL METASURFACE AND THREE-DIMENSIONAL METASURFACE

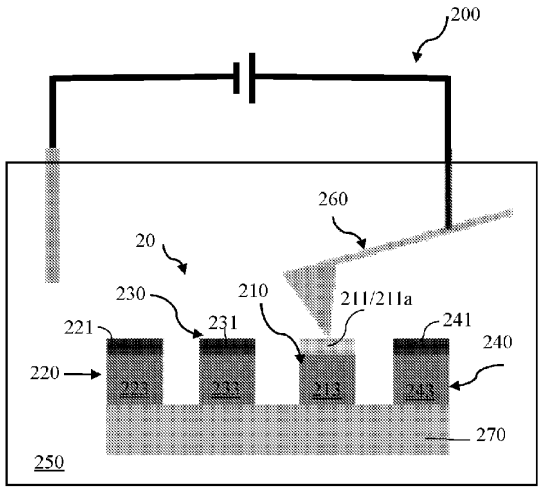


FIG. 2A

(57) Abstract: In some embodiments, a method for forming a three-dimensional metasurface is provided. The method includes: forming a three-dimensional metasurface based on a two-dimensional metasurface, wherein the two-dimensional metasurface comprises a plurality of nanostructures including first to N-th nanostructures, wherein N is an integer greater than or equal to 2, each of the plurality of nanostructures comprising a mask layer and a dielectric layer disposed under the mask layer, wherein the forming a three-dimensional metasurface based on a two-dimensional metasurface comprises: removing an i-th mask layer of the i-th nanostructure of the plurality of nanostructures; and etching an i-th dielectric layer of the i-th nanostructure of the plurality of nanostructure.

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